

SANYO

No.4207

2SK1895

N-Channel MOS Silicon FET

Very High-Speed
Switching Applications**Features**

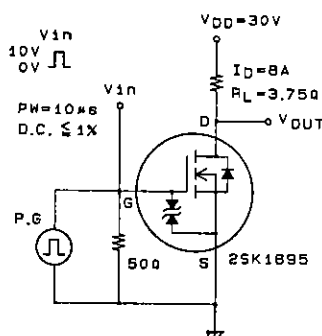
- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating mounting.

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

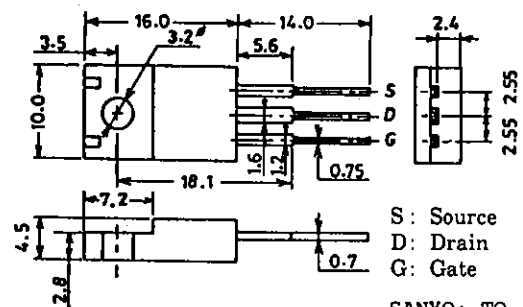
			unit	
Drain to Source Voltage	V_{DS}	60	V	
Gate to Source Voltage	V_{GS}	± 15	V	
Drain Current(DC)	I_D	12	A	
Drain Current(Pulse)	I_{DP}	$PW \leq 10 \mu s, \text{ duty cycle} \leq 1\%$	48	A
Allowable Power Dissipation	P_D	2.0	W	
		$T_c = 25^\circ\text{C}$	25	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$	
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	

Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1\text{mA}, V_{GS} = 0$	60			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100 \mu A, V_{DS} = 0$	± 15			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60\text{V}, V_{GS} = 0$			100	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12\text{V}, V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10\text{V}, I_D = 1\text{mA}$	1.0		2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}, I_D = 8\text{A}$	6.5	10.5		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = 8\text{A}, V_{GS} = 10\text{V}$		60	80	$\text{m}\Omega$
	$R_{DS(on)}$	$I_D = 8\text{A}, V_{GS} = 4\text{V}$		80	110	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{DS} = 20\text{V}, f = 1\text{MHz}$		950		pF
Output Capacitance	C_{oss}	$V_{DS} = 20\text{V}, f = 1\text{MHz}$		250		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 20\text{V}, f = 1\text{MHz}$		50		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		13		ns
Rise Time	t_r	"		40		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		95		ns
Fall Time	t_f	"		80		ns
Diode Forward Voltage	V_{SD}	$I_S = 12\text{A}, V_{GS} = 0$	1.0	1.5		V

Switching Time Test Circuit**Package Dimensions 2063**

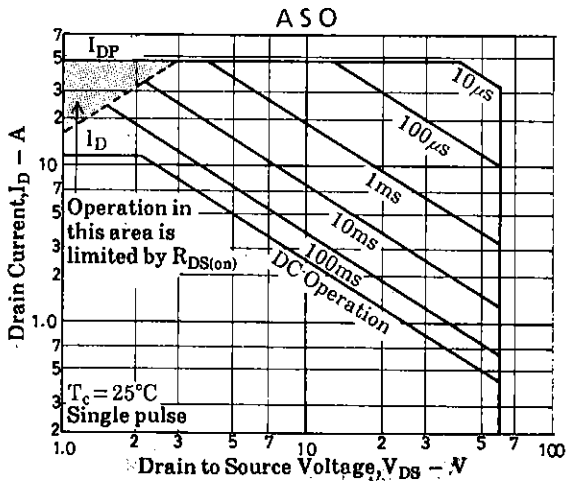
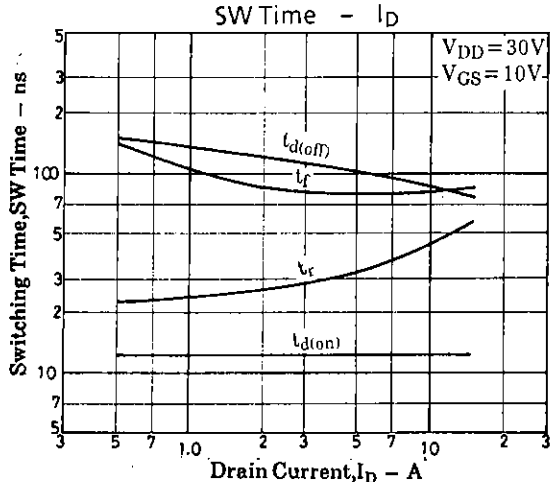
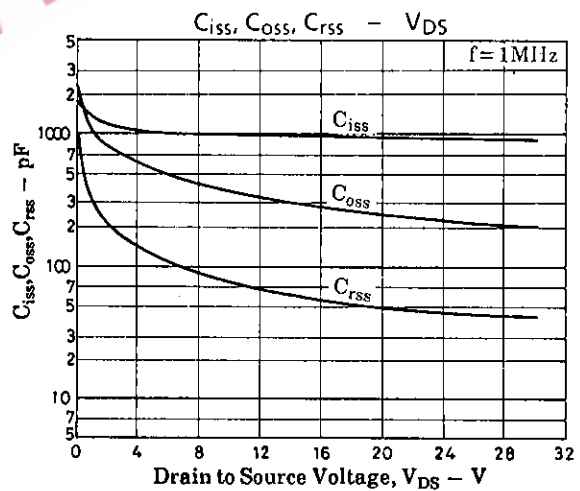
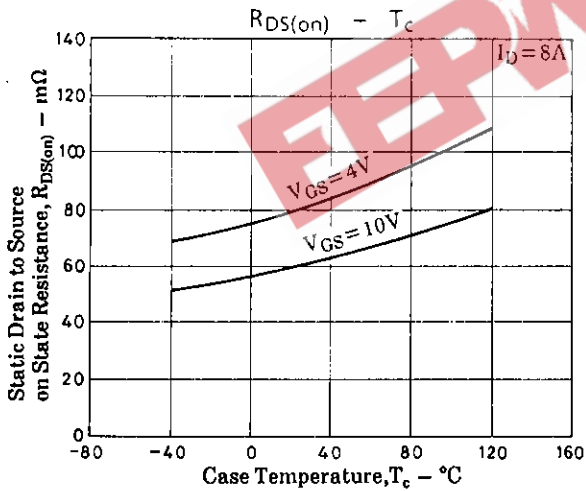
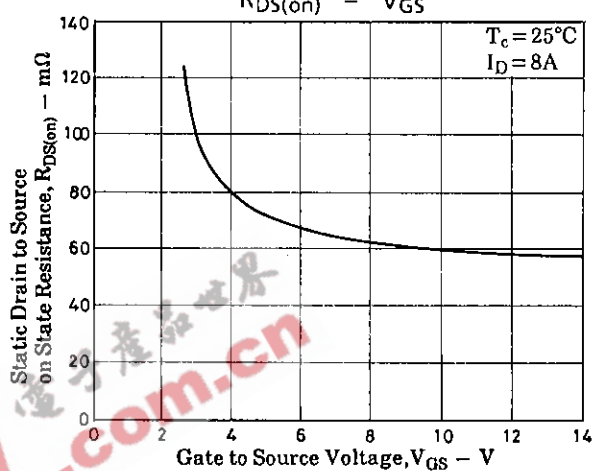
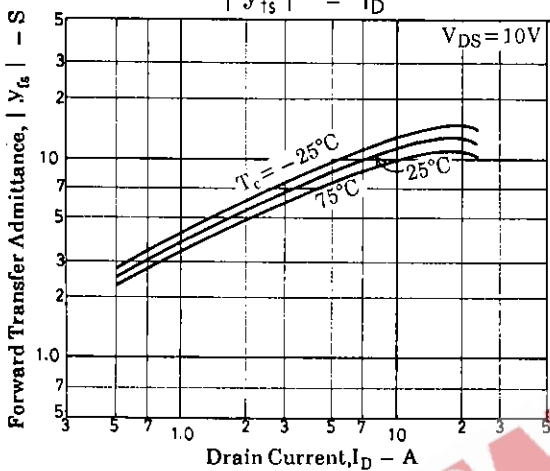
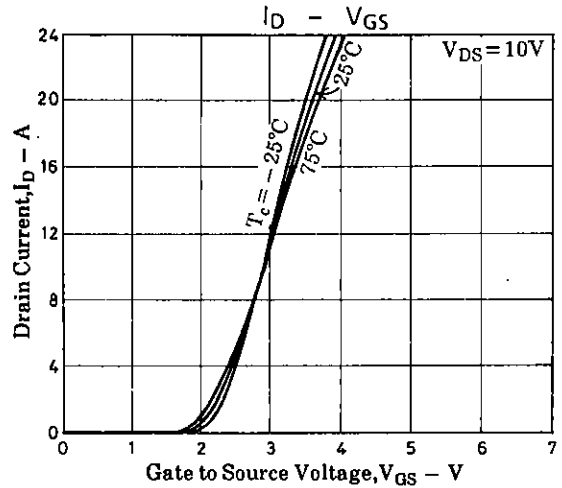
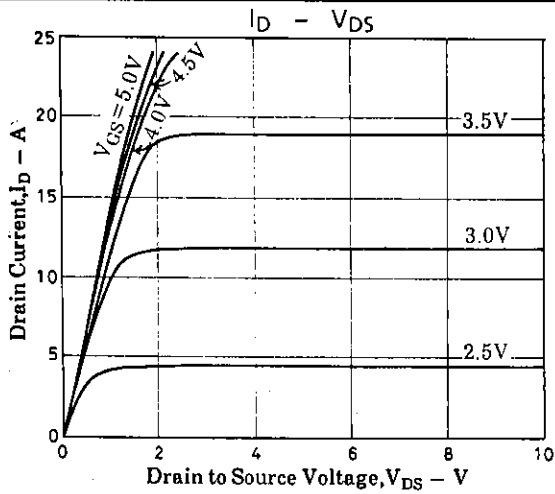
(unit: mm)

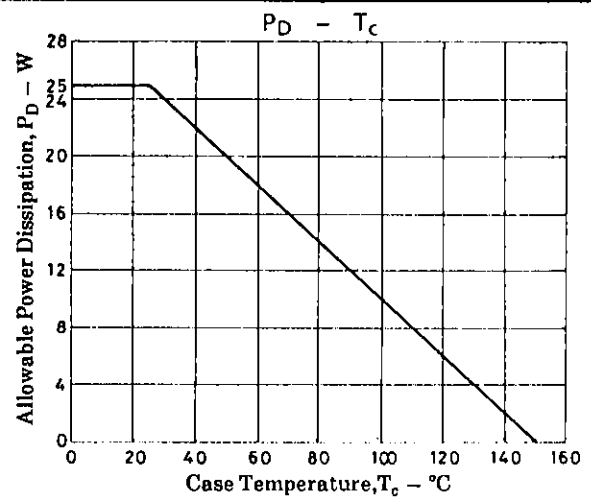
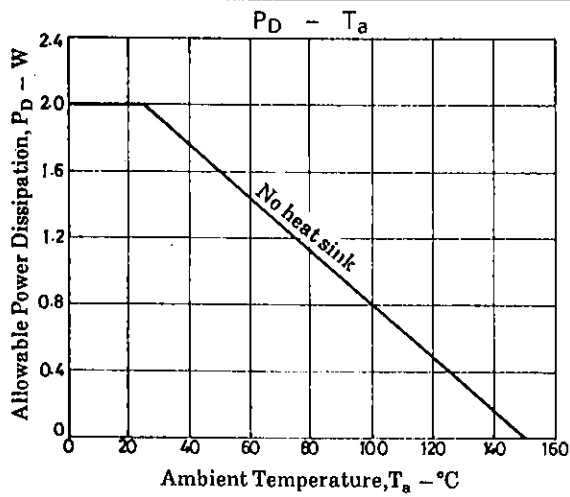


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